

AMENDMENTS TO THE SPECIFICATION

Kindly replace the title of the invention with the following amended title of the invention:

SEMICONDUCTOR TRANSISTOR USING L-SHAPED SPACER ~~AND METHOD OF FABRICATING THE SAME~~

Kindly replace paragraph [0001] with the following amended paragraph:

[0001] The present invention generally relates to a semiconductor device ~~and a method of fabricating the same~~. More specifically, the present invention is directed to a semiconductor transistor using an L-shaped spacer ~~and a method of fabricating the same~~.

Kindly replace the Abstract of the Disclosure with the following amended Abstract of the Disclosure, a clean copy of which is attached at page 9 of this paper:

The present invention provides a semiconductor transistor using an L-shaped spacer ~~and a method of fabricating the same~~. The semiconductor transistor includes a gate pattern formed on a semiconductor substrate and an L-shaped third spacer formed beside the gate pattern and having a horizontal protruding portion. An L-shaped fourth spacer is formed between the third spacer and the gate pattern, and between the third spacer and the substrate. A high-concentration junction area is positioned in the substrate beyond the third spacer, and a low-concentration junction area is positioned under the horizontal protruding portion of the third spacer. A medium-concentration junction area is positioned between the high- and low-concentration junction areas. ~~A method of fabricating the semiconductor transistor includes a process, where the high- and medium- concentration junction areas are formed simultaneously by the same ion-implantation step and the substrate is annealed before forming the low- concentration junction area.~~